

TRADEMARK ASSIGNMENT COVER SHEET

Electronic Version v1.1
Stylesheet Version v1.2

ETAS ID: TM562913

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	RELEASE OF SECURITY INTEREST

CONVEYING PARTY DATA

Name	Formerly	Execution Date	Entity Type
SPECIAL VALUE CONTINUATION PARTNERS, LP		02/19/2020	Limited Partnership:
TENNENBAUM OPPORTUNITIES PARTNERS V, LP		02/19/2020	Limited Partnership:
TGPC SBIC, LP		02/19/2020	Limited Partnership:
TENNEBAUM CAPITAL PARTNERS, LLC		02/19/2020	Limited Liability Company:
EL DORADO INVESTMENT COMPANY		02/19/2020	Corporation:

RECEIVING PARTY DATA

Name:	SORAA, INC.
Street Address:	6500 KAISER DRIVE
City:	FREMONT
State/Country:	CALIFORNIA
Postal Code:	94555
Entity Type:	Corporation: DELAWARE

PROPERTY NUMBERS Total: 7

Property Type	Number	Word Mark
Registration Number:	4581161	SORAA SNAP SYSTEM
Registration Number:	4867520	SORAA
Registration Number:	4150651	SORAA
Registration Number:	4431751	SIMPLY PERFECT LIGHT
Registration Number:	4637522	SIMPLY PERFECT
Registration Number:	4336144	SORAA GAN ON GAN
Registration Number:	4385048	SORAA

CORRESPONDENCE DATA

Fax Number:

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

TRADEMARK

Phone: 4844442262
Email: docketing@fisherbroyles.com, jennifer.chungo@fisherbroyles.com
Correspondent Name: fisherbroyles, llp
Address Line 1: 1650 Market Street
Address Line 2: 36th Floor
Address Line 4: Philadelphia, PENNSYLVANIA 19103

NAME OF SUBMITTER: Stephen driscoll

SIGNATURE: /Stephen Driscoll/

DATE SIGNED: 02/20/2020

Total Attachments: 9

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RELEASE OF SECURITY INTEREST IN INTELLECTUAL PROPERTY

This **RELEASE OF SECURITY INTEREST IN INTELLECTUAL PROPERTY** (the "Release") is dated as of February 19, 2020 by **OBSIDIAN AGENCY SERVICES, INC.**, a California corporation ("Agent"), as agent for **SPECIAL VALUE CONTINUATION PARTNERS, LP, TENNENBAUM OPPORTUNITIES PARTNERS V, LP** and **TCPC SBIC, LP** (collectively, the "Original Lenders"), together with **EL DORADO INVESTMENT COMPANY** and **TENNENBAUM CAPITAL PARTNERS, LLC** (the "Joined Lenders," and collectively, with the Original Lenders, the "Lenders"), in favor of **SORAA, INC.** ("Borrower").

WITNESETH

WHEREAS, Agent, Original Lenders, and Borrower entered into that certain Loan and Security Agreement, dated as of August 29, 2014 (as amended, restated, supplemented, or otherwise modified from time to time) (the "Security Agreement");

WHEREAS, pursuant to the Security Agreement, the Borrower executed and delivered to Agent that certain Intellectual Property Security Agreement dated as of August 29, 2014 (the "IP Security Agreement") and recorded the same with the United States Patent and Trademark Office ("USPTO") on September 5, 2014 at Reel/Frame No. 033691/0582, and on September 5, 2017 at Reel/Frame 05358/0041 pursuant to which the Borrower granted and pledged to Agent for the benefit of the Original Lenders a security interest in all of its right, title and interest in, to and under the Collateral (as defined in the IP Security Agreement);

WHEREAS, pursuant to that certain Release of Security Interest in Intellectual Property dated September 20, 2017 and recorded at Reel/Frame No. 043685/0905, by and between Original Lenders and Borrower ("Partial Release"), Original Lenders released its security interest in certain Collateral ("Released Collateral"), leaving the security interest in the remaining Collateral unaffected thereby ("Remaining Collateral");

WHEREAS, the Joined Lenders did not have any interest in and to the Released Collateral, but possessed a security interest in and to the Remaining Collateral under the terms of the Security Agreement;

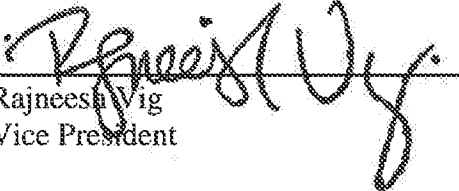
WHEREAS, Borrower has paid in full all of the Obligations (as defined in the Security Agreement), and under the terms of the IP Security Agreement, the security interest in all Collateral, to the extent not already released pursuant to that certain Partial Release, has automatically terminated; and

WHEREAS, Agent is obligated under the terms of the IP Security Agreement to execute, acknowledge, and deliver to Borrower this Release.

NOW, THEREFORE, for good and valuable consideration, the receipt and sufficiency of which are hereby acknowledged, Agent on behalf of itself and the Lenders does hereby (i) terminate the liens and security interest created under the IP Security Agreement in all Collateral, (ii) release its security interest in all Collateral, and (iii) discharge any and all rights, title and interest it has in and the security interest granted to Agent and/or Lenders in all Collateral, in each case to the extent not already released by that certain Partial Release. For the avoidance of doubt, Agent on behalf of itself and the Lenders hereby authorizes and requests the Commissioner of Patents and Trademarks of the United States to record the release, cancellation and termination of the security interests in the Collateral, including the Collateral identified on Schedule I attached hereto.

IN WITNESS WHEREOF, the Agent has caused this Release to be duly executed and delivered as of the date first written above.

OBSIDIAN AGENCY SERVICES, INC.,
on behalf of itself and
SPECIAL VALUE CONTINUATION PARTNERS, LP,
TENNENBAUM OPPORTUNITIES PARTNERS V, LP,
TCPC SBIC, LP,
EL DORADO INVESTMENT COMPANY, and
TENNENBAUM CAPITAL PARTNERS, LLC

By: 
Name: Rajneesh Vig
Title: Vice President

SCHEDULE I
to
RELEASE OF SECURITY INTEREST IN INTELLECTUAL PROPERTY

Title	Jurisdiction	Status	Filing Date	App No.	Grant Date	Patent No.
METHOD AND SURFACE MORPHOLOGY OF NON-POLAR GALLIUM NITRIDE CONTAINING SUBSTRATES	United States of America	Granted	2009-07-02	12/497,289	2012-08-21	8,247,887
METHOD AND SURFACE MORPHOLOGY OF NON-POLAR GALLIUM NITRIDE CONTAINING SUBSTRATES	United States of America	Granted	2012-07-13	13/548,635	2013-11-05	8,575,728
METHOD AND SURFACE MORPHOLOGY OF NON-POLAR GALLIUM NITRIDE CONTAINING SUBSTRATES	United States of America	Granted	2012-07-13	13/548,770	2013-09-03	8,524,578
SURFACE MORPHOLOGY OF NON-POLAR GALLIUM NITRIDE CONTAINING SUBSTRATES	United States of America	Granted	2012-09-17	13/621,485	2014-06-10	8,749,030
SURFACE MORPHOLOGY OF NON-POLAR GALLIUM NITRIDE CONTAINING SUBSTRATES	United States of America	Granted	2014-06-11	14/302,250	2017-11-28	9,831,386
SOLID-STATE OPTICAL DEVICE HAVING ENHANCED INDIUM CONTENT IN ACTIVE REGIONS	United States of America	Granted	2009-06-15	12/484,924	2014-09-30	8,847,249
WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND PHOSPHORS	China	Published	2009-08-03	20098013472 3.8		
White light devices using non-polar or semipolar gallium containing materials and phosphors	United States of America	Granted	2009-08-03	12/534,829	2012-02-28	8,124,996
WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND PHOSPHORS	United States of America	Granted	2012-01-27	13/360,535	2013-10-15	8,558,265
WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND PHOSPHORS	United States of America	Granted	2013-09-24	14/035,693	2015-02-17	8,956,894
WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND PHOSPHORS	United States of America	Allowed	2015-10-14	14/882,893		
GAN CONTAINING OPTICAL DEVICES AND METHOD WITH ESD STABILITY	United States of America	Granted	2010-05-24	12/785,953	2014-07-29	8,791,499
MICROCAVITY LIGHT EMITTING DIODE METHOD OF MANUFACTURE	United States of America	Granted	2009-09-29	12/569,337	2013-01-15	8,354,679
PHOTONIC-CRYSTAL LIGHT EMITTING DIODE AND METHOD OF MANUFACTURE	United States of America	Granted	2009-09-29	12/569,844	2013-06-04	8,455,894
POLARIZATION DIRECTION OF OPTICAL DEVICES USING SELECTED SPATIAL CONFIGURATIONS	United States of America	Granted	2010-03-09	12/720,593	2012-08-21	8,247,886

Title	Jurisdiction	Status	Filing Date	App No.	Grant Date	Patent No.
POLARIZATION DIRECTION OF OPTICAL DEVICES USING SELECTED SPATIAL CONFIGURATIONS	United States of America	Granted	2012-07-19	13/553,691	2015-08-11	9,105,806
METHOD AND STRUCTURE FOR MANUFACTURE OF LIGHT EMITTING DIODE DEVICES USING BULK GAN	United States of America	Granted	2010-03-29	12/749,476	2012-08-28	8,252,662
HIGH INDIUM CONTAINING INGAN SUBSTRATES FOR LONG WAVELENGTH OPTICAL DEVICES	United States of America	Granted	2010-05-21	12/785,404	2012-11-06	8,306,081
POLARIZED WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND TRANSPARENT PHOSPHORS	United States of America	Granted	2010-04-06	12/754,886	2012-10-30	8,299,473
POLARIZED WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND TRANSPARENT PHOSPHORS	United States of America	Granted	2012-09-20	13/623,788	2013-12-31	8,618,560
POLARIZED WHITE LIGHT DEVICES USING NON-POLAR OR SEMIPOLAR GALLIUM CONTAINING MATERIALS AND TRANSPARENT PHOSPHORS	United States of America	Granted	2015-12-22	14/979,027	2019-02-12	RE47241
MULTI COLOR ACTIVE REGIONS FOR WHITE LIGHT EMITTING DIODE	United States of America	Granted	2010-09-13	12/880,803	2012-11-20	8,314,429
GALLIUM-NITRIDE-ON-HANDLE SUBSTRATE MATERIALS AND DEVICES AND METHOD OF MANUFACTURE	United States of America	Granted	2011-01-24	13/012,674	2014-07-22	8,786,053
GALLIUM-NITRIDE-ON-HANDLE SUBSTRATE MATERIALS AND DEVICES AND METHOD OF MANUFACTURE	United States of America	Granted	2014-06-11	14/301,520	2015-02-03	8,946,865
METHOD FOR GROWTH OF INDIUM-CONTAINING NITRIDE FILMS	United States of America	Granted	2012-01-09	13/346,507	2013-07-09	8,482,104
LARGE AREA NITRIDE CRYSTAL AND METHOD FOR MAKING IT	United States of America	Granted	2012-12-31	13/731,453	2017-02-07	9,564,320
Method for growth of a merged crystal by bonding at least a first and second crystal to an adhesion layer to form a tiled substrate and growing a crystalline composition over said tiled substrate	United States of America	Granted	2017-02-07	15/426,770	2019-09-03	10,400,352
Method for growth of a merged crystal by bonding at least a first and second crystal to an adhesion layer to form a tiled substrate and growing a crystalline composition over said tiled substrate	United States of America	Applicati on	2019-08-26	16/550,947		
METHOD OF MAKING BULK INGAN SUBSTRATES AND DEVICES THEREON	United States of America	Granted	2011-10-13	13/272,981	2014-05-20	8,729,559
LARGE AREA NONPOLAR OR SEMIPOLAR GALLIUM AND NITROGEN CONTAINING SUBSTRATE AND RESULTING DEVICES	United States of America	Granted	2012-07-13	13/548,931	2013-07-23	8,492,185
HOMOEPITAXIAL GALLIUM-NITRIDE-BASED LIGHT EMITTING DEVICE AND METHOD FOR PRODUCING	United States of America	Granted	2003-05-19	10/440,574	2005-08-30	6,936,488
LIGHT-BASED SYSTEM FOR DETECTING ANALYTES	United States of America	Granted	2003-12-29	10/746,292	2006-09-05	7,102,158

Title	Jurisdiction	Status	Filing Date	App No.	Grant Date	Patent No.
HOMOEPITAXIAL GALLIUM-NITRIDE-BASED LIGHT EMITTING DEVICE AND METHOD FOR PRODUCING	United States of America	Granted	2004-04-26	10/831,865	2006-05-30	7,053,413
HOMOEPITAXIAL GALLIUM NITRIDE BASED PHOTODETECTOR AND METHOD OF PRODUCING	United States of America	Granted	2001-04-20	09/839,941	2004-10-19	6,806,508
HOMOEPITAXIAL GALLIUM NITRIDE BASED PHOTODETECTOR AND METHOD OF PRODUCING	United States of America	Granted	2004-09-01	10/932,127	2007-11-06	7,291,544
GALLIUM NITRIDE CRYSTAL AND METHOD OF MAKING SAME	China	Granted	2003-12-22	20038010971.2	2009-04-01	ZL20038010971.2
GALLIUM NITRIDE CRYSTAL AND METHOD OF MAKING SAME	Germany (Federal Republic of)	Granted	2003-12-22	03800171.5	2017-04-12	60350118.4
GALLIUM NITRIDE CRYSTAL, HOMOEPITAXIAL GALLIUM-NITRIDE-BASED DEVICES AND METHOD FOR PRODUCING SAME	European Patent	Granted	2003-12-22	03800171.5	2017-04-12	1579486
CRYSTALLINE COMPOSITION, WATER, AND SEMI-CONDUCTOR STRUCTURE	European Patent	Published	2008-01-09	08713079.5		
GALLIUM NITRIDE CRYSTAL, HOMOEPITAXIAL GALLIUM-NITRIDE-BASED DEVICES AND METHOD FOR PRODUCING SAME	European Patent	Published	2003-12-22	17165792.7		
GALLIUM NITRIDE CRYSTAL AND METHOD OF MAKING SAME	United Kingdom	Granted	2003-12-22	03800171.5	2017-04-12	1579486
GALLIUM NITRIDE CRYSTAL AND METHOD OF MAKING SAME	Japan	Granted	2003-12-22	2004-565702	2012-12-21	5159023
GALLIUM NITRIDE CRYSTAL AND METHOD OF MAKING SAME	Japan	Granted	2003-12-22	2012-231681	2015-01-23	5684769
GALLIUM NITRIDE CRYSTAL AND METHOD OF MAKING SAME	Korea, Republic of (KR)	Granted	2003-12-22	2005-7012173	2013-07-30	10-1293352
GALLIUM NITRIDE CRYSTAL AND METHOD OF MAKING SAME	Korea, Republic of (KR)	Granted	2003-12-22	2012-7015773	2013-07-04	10-1284932
GALLIUM NITRIDE CRYSTAL, HOMOEPITAXIAL GALLIUM-NITRIDE-BASED DEVICES AND METHOD FOR PRODUCING SAME	Singapore	Granted	2003-12-22	200503618-1	2007-07-31	112630
GALLIUM NITRIDE CRYSTAL AND METHOD OF MAKING SAME	United States of America	Granted	2002-12-27	10/329,981	2006-08-29	7,098,487
GALLIUM NITRIDE CRYSTALS AND WAFERS AND METHOD OF MAKING	United States of America	Granted	2004-12-13	11/010,507	2006-07-18	7,078,731
Method of making a gallium nitride crystalline composition having a low dislocation density	United States of America	Granted	2006-11-09	11/558,048	2016-03-08	9,279,193
GALLIUM NITRIDE CRYSTAL AND METHOD OF MAKING SAME	United States of America	Granted	2006-10-26	11/588,181	2013-01-22	8,357,945
GALLIUM NITRIDE CRYSTALS AND WAFERS AND METHOD OF MAKING	United States of America	Granted	2006-11-13	11/559,146	2010-08-31	7,786,503
Crystalline composition, wafer, device, and associated method	United States of America	Granted	2007-01-09	11/621,556	2010-12-28	7,859,008
Crystalline composition, wafer, and semiconductor structure	United States of America	Granted	2007-01-09	11/621,560	2009-12-29	7,638,815
CRYSTALLINE GALLIUM NITRIDE CONTAINING FLOURINE	United States of America	Granted	2016-03-04	15/061,069	2019-02-19	10208396

Title	Jurisdiction	Status	Filing Date	App No.	Grant Date	Patent No.
METHOD ASSOCIATED WITH A CRYSTALLINE COMPOSITION AND WAFER	United States of America	Published	2019-01-11	16/246,065		
HOMOEPITAXIAL GALLIUM-NITRIDE-BASED VERTICAL CAVITY SURFACE-EMITTING LASER (VCSEL) AND METHOD FOR PRODUCING	Germany (Federal Republic of)	Granted	2004-10-22	04796085.1	2012-08-01	1680817
HOMOEPITAXIAL GALLIUM-NITRIDE-BASED VERTICAL CAVITY SURFACE-EMITTING LASER (VCSEL) AND METHOD FOR PRODUCING	European Patent	Granted	2004-10-22	04796085.1	2012-08-01	1680817
HOMOEPITAXIAL GALLIUM-NITRIDE-BASED VERTICAL CAVITY SURFACE-EMITTING LASER (VCSEL) AND METHOD FOR PRODUCING	France	Granted	2004-10-22	04796085.1	2012-08-01	1680817
HOMOEPITAXIAL GALLIUM-NITRIDE-BASED VERTICAL CAVITY SURFACE-EMITTING LASER (VCSEL) AND METHOD FOR PRODUCING	Korea, Republic of (KR)	Granted	2004-10-22	2005-7020687	2013-07-30	10-1293307
HOMOEPITAXIAL GALLIUM-NITRIDE-BASED VERTICAL CAVITY SURFACE-EMITTING LASER (VCSEL) AND METHOD FOR PRODUCING	Netherlands	Granted	2004-10-22	04796085.1	2012-08-01	1680817
HOMOEPITAXIAL GALLIUM-NITRIDE-BASED VERTICAL CAVITY SURFACE-EMITTING LASER (VCSEL) AND METHOD FOR PRODUCING	United States of America	Granted	2003-10-24	10/693,803	2006-03-07	7,009,215
METHOD FOR REDUCING DEFECT CONCENTRATIONS IN CRYSTALS	United States of America	Granted	2005-12-12	11/300,660	2012-07-10	8,216,370
OXYGEN-DOPED GROUP III METAL NITRIDE AND METHOD OF MANUFACTURE	United States of America	Allowed	2018-01-09	15/865,391		
HOMOEPITAXIAL GALLIUM-NITRIDE-BASED VERTICAL CAVITY SURFACE-EMITTING LASER (VCSEL) AND METHOD FOR PRODUCING	China	Granted	2004-10-22	200480015116.	2009-03-25	ZL200480015116.7

Patent Application Title	Country	Status	Filed Date	Application Number	Grant Date	Patent No.
INDIUM GALLIUM NITRIDE LIGHT EMITTING DEVICES	United States of America	Granted	2013-10-15	14/054,234	2018-05-22	9,978,904
DENSE-LUMINESCENT-MATERIALS-COATED VIOLET LEDS	United States of America	Granted	2013-12-19	14/135,098	2017-09-12	9,761,763
ACCESSORIES FOR LED LAMP SYSTEMS	United States of America	Granted	2014-01-28	14/166,692	2016-11-08	9,488,324
GALLIUM AND NITROGEN CONTAINING TRIANGULAR OR DIAMOND-SHAPED CONFIGURATION FOR OPTICAL DEVICES	United States of America	Granted	2012-01-24	13/357,578	2016-09-20	9,450,143
COMPACT LENS FOR HIGH INTENSITY LIGHT SOURCE	United States of America	Granted	2013-04-18	13/865,760	2016-04-12	9,310,052
POWER LIGHT EMITTING DIODE AND METHOD WITH UNIFORM CURRENT DENSITY OPERATION	United States of America	Granted	2013-09-27	14/040,379	2016-03-22	9,293,644
SYSTEM AND METHOD FOR SELECTED PUMP LED _s WITH MULTIPLE PHOSPHORS	United States of America	Granted	2011-08-16	13/211,145	2016-03-22	9,293,667
LIGHT EMITTING DIODES WITH LOW REFRACTIVE INDEX MATERIAL LAYERS TO REDUCE LIGHT GUIDING EFFECTS	United States of America	Granted	2013-03-06	13/787,582	2016-02-23	9,269,876
MISCUT BULK SUBSTRATES	United States of America	Granted	2012-03-27	13/431,834	2016-01-12	9,236,530
HIGH-TEMPERATURE ULTRA-LOW RIPPLE MULTI-STAGE LED DRIVER AND LED CONTROL CIRCUITS	United States of America	Granted	2013-11-08	14/075,936	2015-12-15	9,215,764
ACCESSORIES FOR LED LAMPS	United States of America	Granted	2013-08-29	14/014,112	2015-08-18	9,109,760
METHOD FOR MANUFACTURE OF BRIGHT GAN LEDS USING A SELECTIVE REMOVAL PROCESS	United States of America	Granted	2011-11-23	13/304,182	2014-12-16	8,912,025
SYSTEM AND METHOD FOR PROVIDING COLOR LIGHT SOURCES IN PROXIMITY TO PREDETERMINED WAVELENGTH CONVERSION STRUCTURES	United States of America	Granted	2014-04-18	14/256,670	2014-12-09	8,905,588
ACCESSORIES FOR LED LAMPS	United States of America	Granted	2013-06-04	13/909,752	2014-11-18	8,888,332
SOLID-STATE OPTICAL DEVICE HAVING ENHANCED INDIUM CONTENT IN ACTIVE REGIONS	United States of America	Granted	2009-06-15	12/484,924	2014-09-30	8,847,249
ILLUMINATION SOURCE WITH DIRECT DIE PLACEMENT	United States of America	Granted	2013-08-05	13/959,422	2014-09-09	8,829,774
HIGH INTENSITY LIGHT SOURCE	United States of America	Granted	2011-10-07	13/269,193	2014-08-12	8,803,452
SYSTEM AND METHOD FOR PROVIDING COLOR LIGHT SOURCES IN PROXIMITY TO PREDETERMINED WAVELENGTH CONVERSION STRUCTURES	United States of America	Granted	2011-12-16	13/328,978	2014-06-03	8,740,413
POWER LIGHT EMITTING DIODE AND METHOD WITH CURRENT DENSITY OPERATION	United States of America	Granted	2013-06-28	13/931,359	2014-04-01	8,686,458
GALLIUM AND NITROGEN CONTAINING TRILATERAL	United States of America	Granted	2011-10-25	13/281,221	2014-04-01	8,686,431

Patent Application Title	Country	Status	Filed Date	Application Number	Grant Date	Patent No.
CONFIGURATION FOR OPTICAL DEVICES						
SYSTEM AND METHOD FOR LED PACKAGING	United States of America	Granted	2012-05-29	13/482,956	2014-03-18	8,674,395
ILLUMINATION SOURCE WITH REDUCED INNER CORE SIZE	United States of America	Granted	2011-02-11	13/025,833	2014-02-04	8,643,257
ILLUMINATION SOURCE AND MANUFACTURING METHODS	United States of America	Granted	2011-02-11	13/025,849	2013-12-31	8,618,742
METHOD AND SYSTEM FOR DICING SUBSTRATES CONTAINING GALLIUM AND NITROGEN MATERIAL	United States of America	Granted	2011-11-17	13/298,617	2013-12-03	8,597,967
HEATSINK	United States of America	Granted	2012-06-04	29/423,725	2013-12-03	D694,722
OPTICAL DEVICES HAVING REFLECTION MODE WAVELENGTH MATERIAL	United States of America	Granted	2012-08-31	13/600,988	2013-11-05	8,575,642
HIGH TEMPERATURE LED SYSTEM USING AN AC POWER SOURCE	United States of America	Granted	2011-11-17	13/298,905	2013-09-24	8,541,951
ILLUMINATION SOURCE WITH DIRECT DIE PLACEMENT	United States of America	Granted	2011-02-11	13/025,791	2013-09-03	8,525,396
POWER LIGHT EMITTING DIODE AND METHOD WITH CURRENT DENSITY OPERATION	United States of America	Granted	2010-09-20	12/936,238	2013-08-06	8,502,465
TECHNIQUES OF FORMING OHMIC CONTACTS ON GAN LIGHT EMITTING DIODES	United States of America	Granted	2012-03-13	13/419,325	2013-03-05	8,389,305
MODULAR LED LAMP AND MANUFACTURING METHODS	United States of America	Granted	2011-02-11	13/025,860	2012-12-04	8,324,835
SINGULATION METHOD AND RESULTING DEVICE OF THICK GALLIUM AND NITROGEN CONTAINING SUBSTRATES	United States of America	Granted	2011-06-17	13/163,498	2012-11-20	8,313,964
GALLIUM AND NITROGEN CONTAINING TRIANGULAR OR DIAMOND-SHAPED CONFIGURATION FOR OPTICAL DEVICES	United States of America	Granted	2011-06-17	13/163,482	2012-10-23	8,293,551
OPTICAL DEVICE WITH WAVELENGTH SELECTIVE REFLECTOR	United States of America	Granted	2010-10-28	12/914,789	2012-09-18	8,269,245
HEATSINK	United States of America	Granted	2011-08-15	29/399,523	2012-07-03	D662,899
HEATSINK FOR LED	United States of America	Granted	2011-08-15	29/399,524	2012-07-03	D662,900
SYSTEM AND METHOD FOR LED PACKAGING	United States of America	Granted	2010-09-10	12/879,784	2012-06-26	8,207,554
BACK-END PROCESSES FOR SUBSTRATES RE-USE	United States of America	Granted	2010-08-17	12/858,379	2012-04-10	8,153,475
TECHNIQUES OF FORMING OHMIC CONTACTS ON GAN LIGHT EMITTING DIODES	United States of America	Granted	2011-07-15	13/184,160	2012-04-03	8,148,180

Mark	Country	Status	Appl. No.	Date	Reg. No.	Date
SORAA SNAP SYSTEM	United States of America	Registered	85895887	2013-04-04	4581161	2014-08-05
SORAA	United States of America	Registered	86/058,247	2013-09-06	4867520	2015-12-08
SORAA	United States of America	Registered	77/982,688	2009-10-05	4150651	2012-05-29
SIMPLY PERFECT LIGHT	United States of America	Registered	85870246	2013-03-07	4431751	2013-11-12
SIMPLY PERFECT	United States of America	Registered	85495244	2011-12-14	4637522	2014-11-11
SORAA GAN ON GAN	United States of America	Registered	85/593,900	2012-04-10	4336144	2013-05-14
SORAA	United States of America	Registered	85/594,716	2012-04-11	4385048	2013-08-13